

## N-Channel 200-V (D-S) MOSFET

### Key Features:

- Low  $r_{DS(on)}$  trench technology
- Low thermal impedance
- Fast switching speed

### Typical Applications:

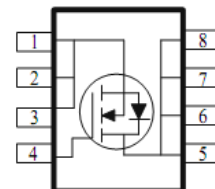
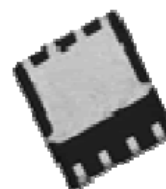
- PoE PSE and PD Circuits
- LED Inverter Circuits
- 48V-Input DC/DC Conversion Circuits

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ (m $\Omega$ )	$I_D$ (A)
200	158 @ $V_{GS} = 10V$	4.6
	195 @ $V_{GS} = 6V$	4.2



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

DFN5X6-8L



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		$V_{DS}$	200	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	4.6	A
	$T_A = 70^\circ\text{C}$		3.7	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	15	
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	5	A
Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	5	W
	$T_A = 70^\circ\text{C}$		3.2	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{\theta JA}$	25	$^\circ\text{C/W}$
	Steady State		65	

### Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

## Electrical Characteristics

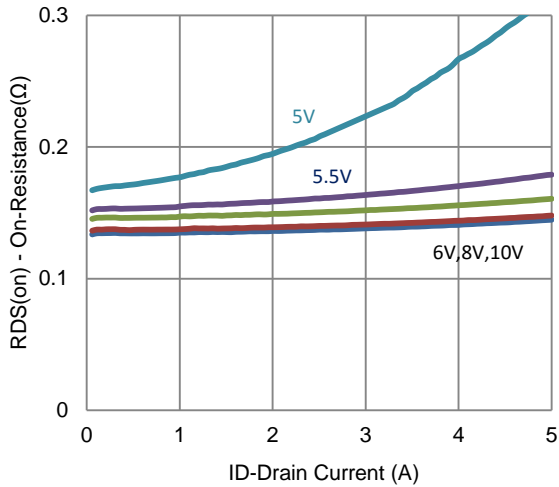
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 160 V, V_{GS} = 0 V$			1	uA
		$V_{DS} = 160 V, V_{GS} = 0 V, T_J = 55^\circ C$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	7			A
Drain-Source On-Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 1 A$			158	mΩ
		$V_{GS} = 6 V, I_D = 0.8 A$			195	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 V, I_D = 5 A$		9		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.5 A, V_{GS} = 0 V$		0.77		V
<b>Dynamic <sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 100 V, V_{GS} = 6 V,$ $I_D = 1 A$		13		nC
Gate-Source Charge	$Q_{gs}$			4.5		
Gate-Drain Charge	$Q_{gd}$			5.9		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 100 V, R_L = 100 \Omega,$ $I_D = 1 A,$ $V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		8		ns
Rise Time	$t_r$			9		
Turn-Off Delay Time	$t_{d(off)}$			28		
Fall Time	$t_f$			11		
Input Capacitance	$C_{iss}$	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 \text{ Mhz}$		626		pF
Output Capacitance	$C_{oss}$			83		
Reverse Transfer Capacitance	$C_{rss}$			48		

## Notes

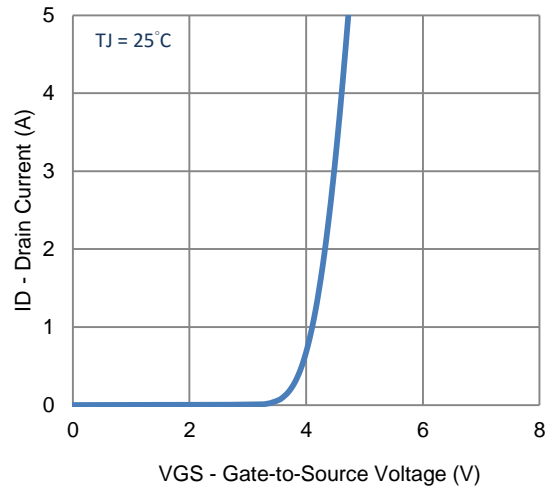
- Pulse test:  $PW \leq 300 \mu s$  duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.

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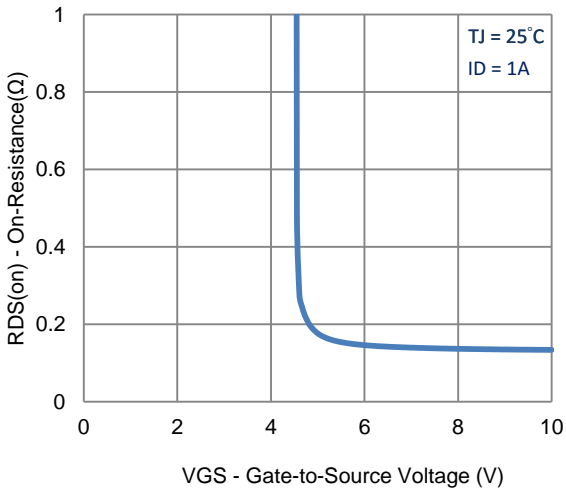
Typical Electrical Characteristics



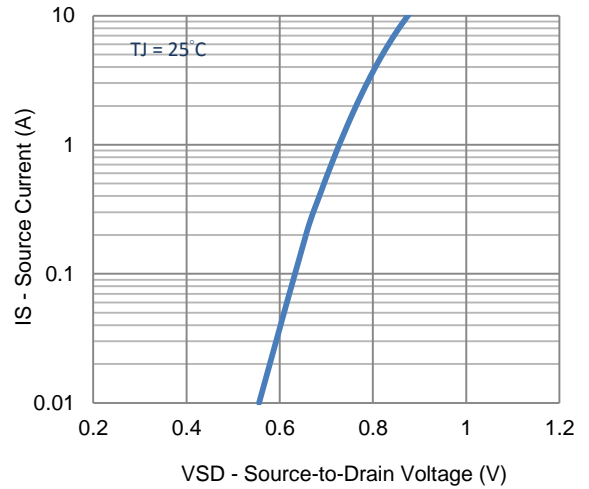
1. On-Resistance vs. Drain Current



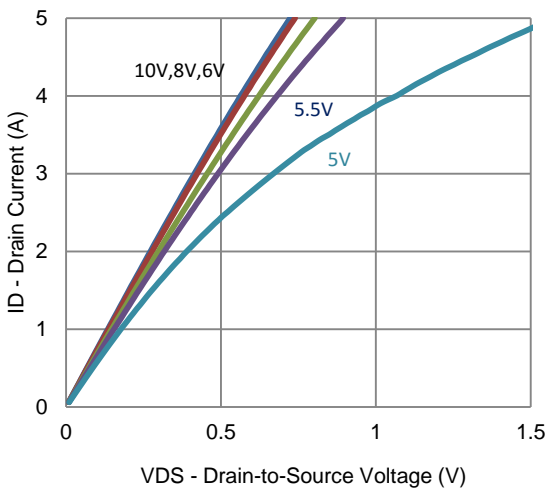
2. Transfer Characteristics



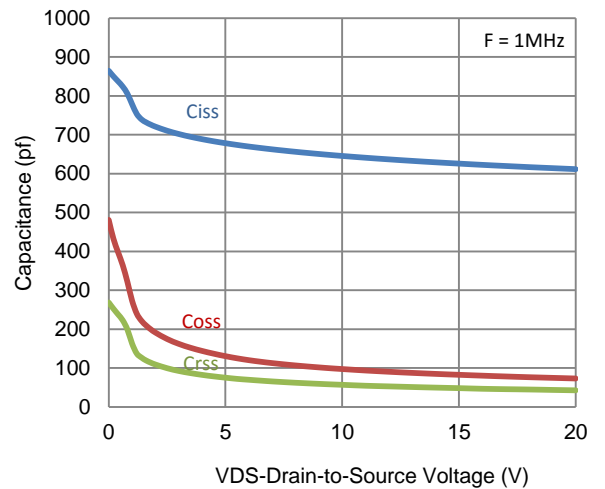
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

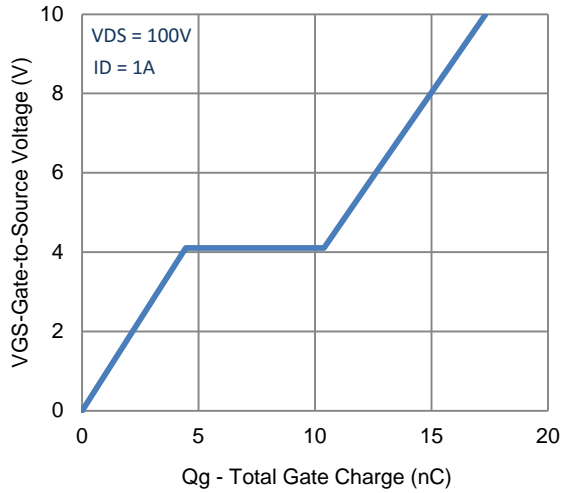


5. Output Characteristics

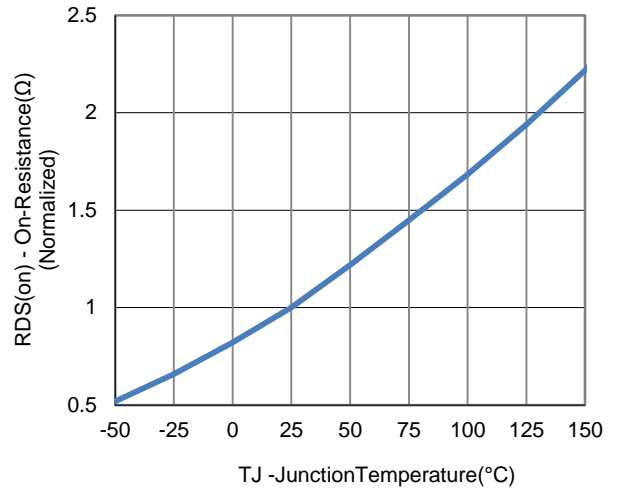


6. Capacitance

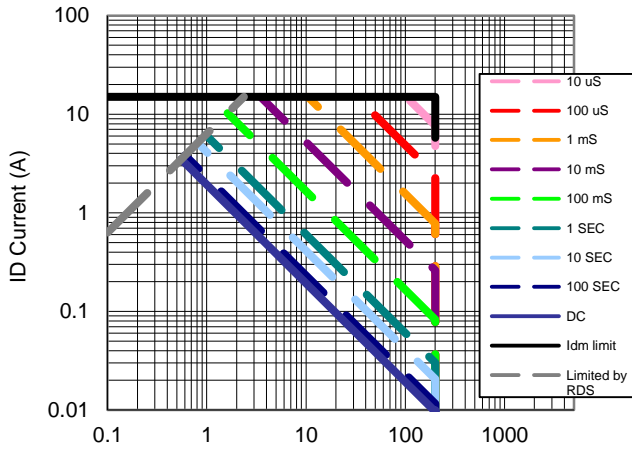
Typical Electrical Characteristics



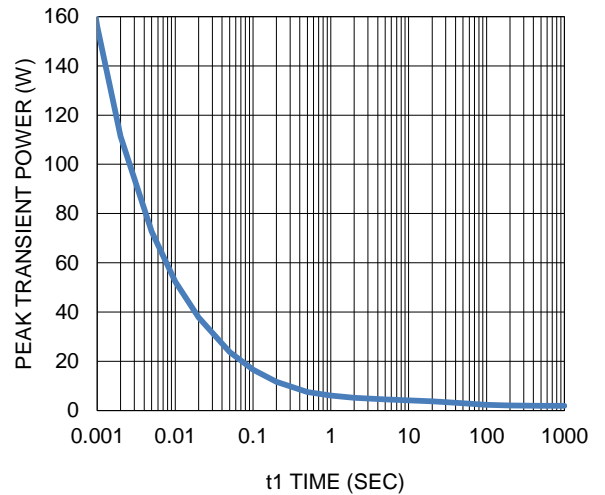
7. Gate Charge



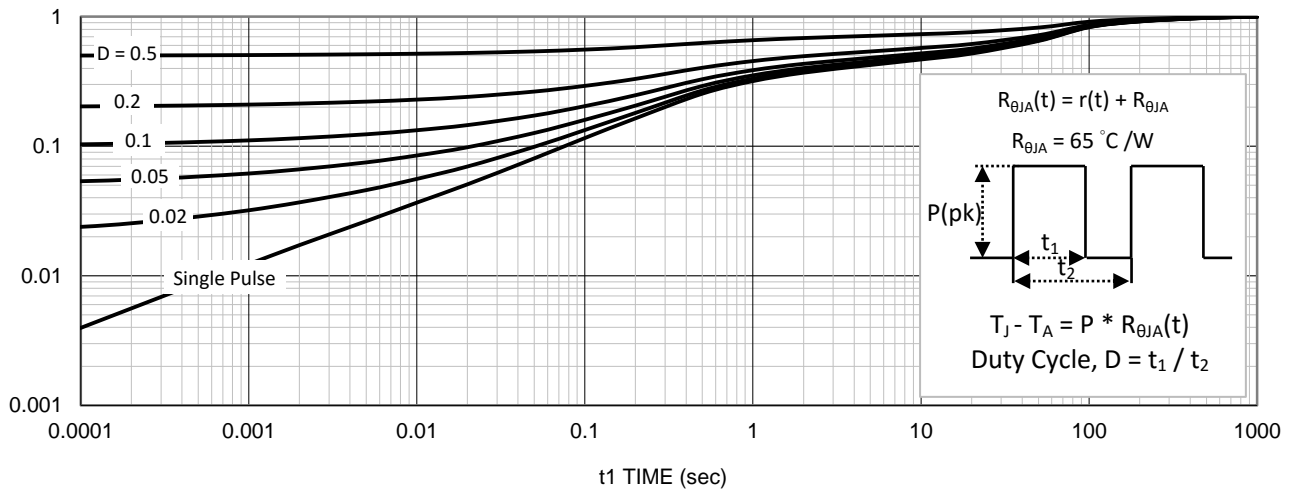
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

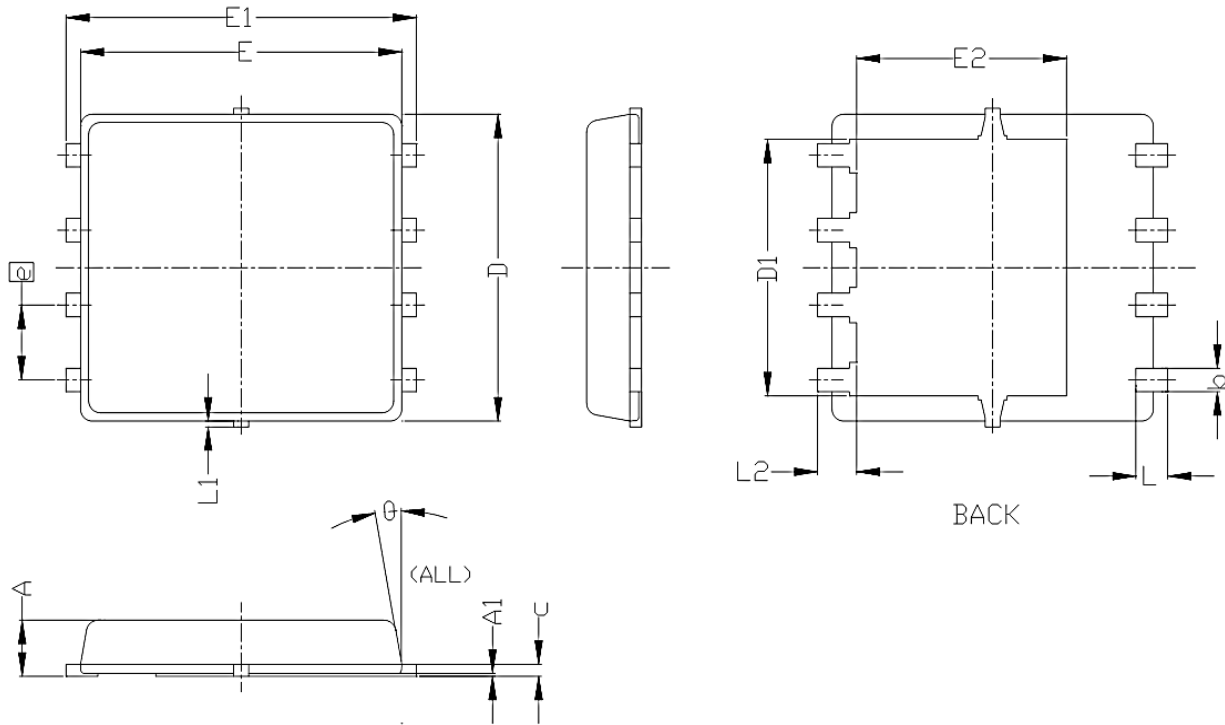


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.20 BSC			0.205 BSC		
D1	4.35 BSC			0.171 BSC		
E	5.55 BSC			0.219 BSC		
E1	6.05 BSC			0.238 BSC		
E2	3.62 BSC			0.143 BSC		
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
$\theta$	0°	---	10°	0°	---	10°